

IN THE CLAIMS:

This listing of claims will replace prior version, and listings, of claims in the application:

1. (Currently amended) A semiconductor device comprising:
 - a gate electrode formed on an insulating surface;
 - a gate insulating film comprising at least a single layer on said gate electrode; and
 - ~~a crystalline semiconductor film comprising~~ a source region, a drain region, and a channel formation region formed between said source region and said drain region, the respective regions being in contact with said gate insulating film;

wherein said gate insulating film includes a layer of a silicon nitride oxide film containing boron.
2. (Previously presented) A semiconductor device according to claim 1, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.
3. (Previously presented) A semiconductor device according to claim 1, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.
4. (Previously presented) A semiconductor device according to claim 1, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.
5. (Previously presented) A semiconductor device according to claim 4, wherein said

electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

6. (Previously presented) A semiconductor device according to claim 4, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

7. (Previously presented) A semiconductor device comprising:
a source region, a drain region, and a channel formation region formed between said source region and said drain region, the respective regions being in contact with an insulating surface;

a gate insulating film comprising at least a single layer on said channel formation region; and

a gate electrode to be in contact with said gate insulating film;
wherein said gate insulating film includes a layer of a silicon nitride oxide film containing boron.

8. (Previously presented) A semiconductor device according to claim 7, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

9. (Previously presented) A semiconductor device according to claim 7, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms %.

10. (Previously presented) A semiconductor device according to claim 7, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

11. (Previously presented) A semiconductor device according to claim 10, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, and EC display device, and an image sensor.

12. (Previously presented) A semiconductor device according to claim 10, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

13. (Currently amended) A semiconductor device comprising:
an insulating film formed on an insulating surface; and
a semiconductor component formed on said insulating film, said semiconductor component comprising ~~crystalline semiconductor film as a source region, a drain region, and a~~ a channel formation region formed between the source region and the drain region, the respective regions being in contact with said insulating thereof;

wherein said insulating film is a silicon nitride oxide film containing boron.

14. (Previously presented) A semiconductor device according to claim 13, wherein a

composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

15. (Previously presented) A semiconductor device according to claim 13, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

16. (Previously presented) A semiconductor device according to claim 13, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

17. (Previously presented) A semiconductor device according to claim 16, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

18. (Previously presented) A semiconductor device according to claim 16, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

19. (Currently Amended) A semiconductor device comprising:
a semiconductor component formed on an insulating surface, said semiconductor component comprising a source region, a drain region, and a channel formation region; and
an insulating film for protecting said semiconductor component, said insulation film being in contact with the source region, the drain region, and the channel formation region said

~~semiconductor component comprising crystalline semiconductor film as a channel formation region thereof;~~

wherein said insulating film is a silicon nitride oxide film containing boron.

20. (Previously presented) A semiconductor device according to claim 19, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

21. (Previously presented) A semiconductor device according to claim 19, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

22. (Previously presented) A semiconductor device according to claim 19, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

23. (Previously presented) A semiconductor device according to claim 22, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

24. (Previously presented) A semiconductor device according to claim 22, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

25-31. (Canceled)

32. (New) A semiconductor device according to claim 1, wherein an internal stress of said silicon nitride oxide film is a range of 5×10^{10} dyn/cm² to 5×10^{10} dyn/cm².

33. (New) A semiconductor device according to claim 7, wherein an internal stress of said silicon nitride oxide film is a range of 5×10^{10} dyn/cm² to 5×10^{10} dyn/cm².

34. (New) A semiconductor device according to claim 13, wherein an internal stress of said silicon nitride oxide film is a range of 5×10^{10} dyn/cm² to 5×10^{10} dyn/cm².

35. (New) A semiconductor device according to claim 19, wherein an internal stress of said silicon nitride oxide film is a range of 5×10^{10} dyn/cm² to 5×10^{10} dyn/cm².